

# SGH10N120RUFD

## Short Circuit Rated IGBT

### General Description

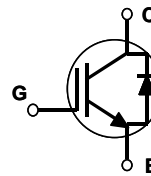
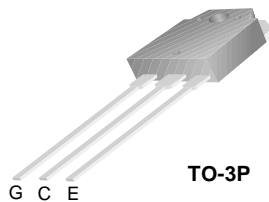
Fairchild's RUF D series of Insulated Gate Bipolar Transistors (IGBTs) provides low conduction and switching losses as well as short circuit ruggedness. The RUF D series is designed for applications such as motor control, uninterrupted power supplies (UPS) and general inverters where short circuit ruggedness is a required feature.

### Features

- Short circuit rated 10 $\mu$ s @ T<sub>C</sub> = 100°C, V<sub>GE</sub> = 15V
- High speed switching
- Low saturation voltage : V<sub>CE(sat)</sub> = 2.3 V @ I<sub>C</sub> = 10A
- High input impedance
- CO-PAK, IGBT with FRD : t<sub>rr</sub> = 65ns (typ.)

### Applications

AC & DC motor controls, general purpose inverters, robotics, and servo controls.



### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Description	SGH10N120RUFD	Units
V <sub>CES</sub>	Collector-Emitter Voltage	1200	V
V <sub>GES</sub>	Gate-Emitter Voltage	± 25	V
I <sub>C</sub>	Collector Current @ T <sub>C</sub> = 25°C	16	A
	Collector Current @ T <sub>C</sub> = 100°C	10	A
I <sub>CM(1)</sub>	Pulsed Collector Current	30	A
I <sub>F</sub>	Diode Continuous Forward Current @ T <sub>C</sub> = 100°C	10	A
I <sub>FM</sub>	Diode Maximum Forward Current	60	A
T <sub>SC</sub>	Short Circuit Withstand Time @ T <sub>C</sub> = 100°C	10	μs
P <sub>D</sub>	Maximum Power Dissipation @ T <sub>C</sub> = 25°C	125	W
	Maximum Power Dissipation @ T <sub>C</sub> = 100°C	50	W
T <sub>J</sub>	Operating Junction Temperature	-55 to +150	°C
T <sub>stg</sub>	Storage Temperature Range	-55 to +150	°C
T <sub>L</sub>	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	300	°C

**Notes :**

(1) Repetitive rating : Pulse width limited by max. junction temperature

### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
R <sub>θJC</sub> (IGBT)	Thermal Resistance, Junction-to-Case	--	1.0	°C/W
R <sub>θJC</sub> (DIODE)	Thermal Resistance, Junction-to-Case	--	1.5	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient	--	40	°C/W

**Electrical Characteristics of the IGBT**  $T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
<b>Off Characteristics</b>						
$BV_{CES}$	Collector-Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 1mA$	1200	--	--	V
$\Delta BV_{CES}/\Delta T_J$	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0V, I_C = 1mA$	--	0.6	--	$V/^\circ\text{C}$
$I_{CES}$	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0V$	--	--	1	mA
$I_{GES}$	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$	--	--	$\pm 100$	nA

**On Characteristics**

$V_{GE(th)}$	G-E Threshold Voltage	$I_C = 10mA, V_{CE} = V_{GE}$	3.5	5.5	7.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 10A, V_{GE} = 15V$	--	2.3	3.0	V
		$I_C = 16A, V_{GE} = 15V$	--	2.8	--	V

**Dynamic Characteristics**

$C_{ies}$	Input Capacitance	$V_{CE} = 30V, V_{GE} = 0V,$ $f = 1MHz$	--	950	--	pF
$C_{oes}$	Output Capacitance		--	75	--	pF
$C_{res}$	Reverse Transfer Capacitance		--	30	--	pF

**Switching Characteristics**

$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 600V, I_C = 10A,$ $R_G = 25\Omega, V_{GE} = 15V,$ Inductive Load, $T_C = 25^\circ\text{C}$	--	20	--	ns
$t_r$	Rise Time		--	60	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	60	110	ns
$t_f$	Fall Time		--	150	300	ns
$E_{on}$	Turn-On Switching Loss		--	0.65	--	mJ
$E_{off}$	Turn-Off Switching Loss		--	0.65	--	mJ
$E_{ts}$	Total Switching Loss	--	1.3	1.85	mJ	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 600V, I_C = 10A,$ $R_G = 25\Omega, V_{GE} = 15V,$ Inductive Load, $T_C = 125^\circ\text{C}$	--	20	--	ns
$t_r$	Rise Time		--	70	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	80	150	ns
$t_f$	Fall Time		--	200	400	ns
$E_{on}$	Turn-On Switching Loss		--	0.75	--	mJ
$E_{off}$	Turn-Off Switching Loss		--	1.00	--	mJ
$E_{ts}$	Total Switching Loss	--	1.75	2.54	mJ	
$T_{sc}$	Short Circuit Withstand Time	$V_{CC} = 600V, V_{GE} = 15V$ @ $T_C = 100^\circ\text{C}$	10	--	--	$\mu\text{s}$
$Q_g$	Total Gate Charge	$V_{CE} = 600V, I_C = 10A,$ $V_{GE} = 15V$	--	50	75	nC
$Q_{ge}$	Gate-Emitter Charge		--	6	9	nC
$Q_{gc}$	Gate-Collector Charge		--	25	40	nC
$L_e$	Internal Emitter Inductance	Measured 5mm from PKG	--	14	--	nH

**Electrical Characteristics of DIODE**  $T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units	
$V_{FM}$	Diode Forward Voltage	$I_F = 10A$	$T_C = 25^\circ\text{C}$	--	2.9	3.5	V
			$T_C = 100^\circ\text{C}$	--	2.7	--	
$t_{rr}$	Diode Reverse Recovery Time	$I_F = 10A$ $di/dt = 200A/\mu\text{s}$	$T_C = 25^\circ\text{C}$	--	65	100	ns
			$T_C = 100^\circ\text{C}$	--	90	--	
$I_{rr}$	Diode Peak Reverse Recovery Current	$I_F = 10A$ $di/dt = 200A/\mu\text{s}$	$T_C = 25^\circ\text{C}$	--	6.0	8.0	A
			$T_C = 100^\circ\text{C}$	--	7.5	--	
$Q_{rr}$	Diode Reverse Recovery Charge	$I_F = 10A$ $di/dt = 200A/\mu\text{s}$	$T_C = 25^\circ\text{C}$	--	195	400	nC
			$T_C = 100^\circ\text{C}$	--	300	--	

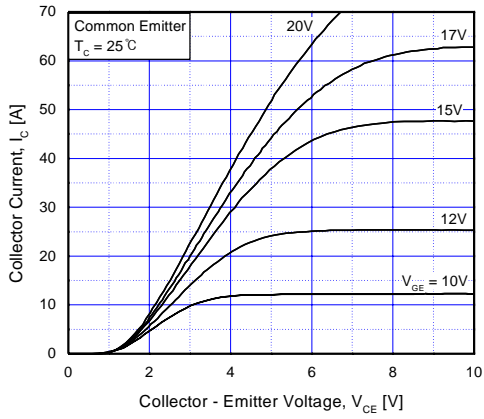


Fig 1. Typical Output Characteristics

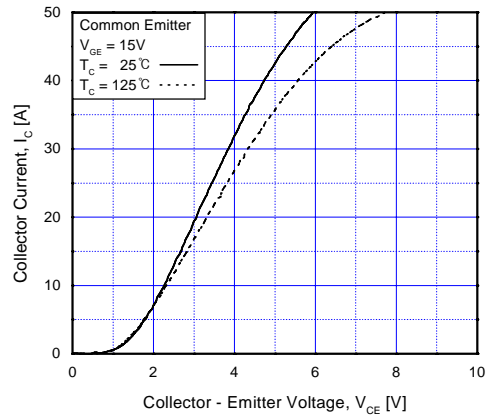


Fig 2. Typical Saturation Voltage Characteristics

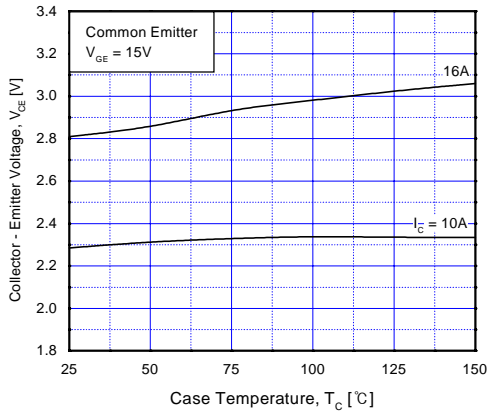


Fig 3. Saturation Voltage vs. Case Temperature at Variant Current Level

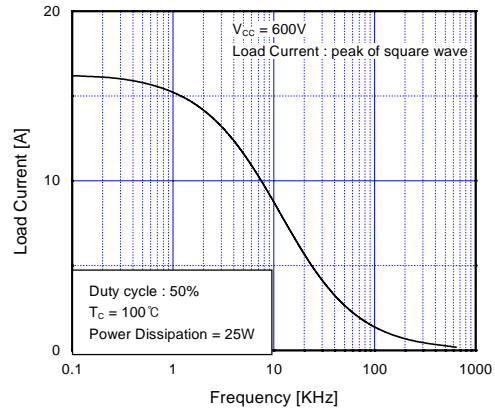


Fig 4. Load Current vs. Frequency

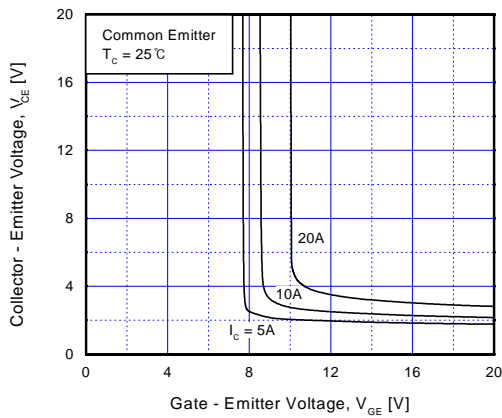


Fig 5. Saturation Voltage vs.  $V_{GE}$

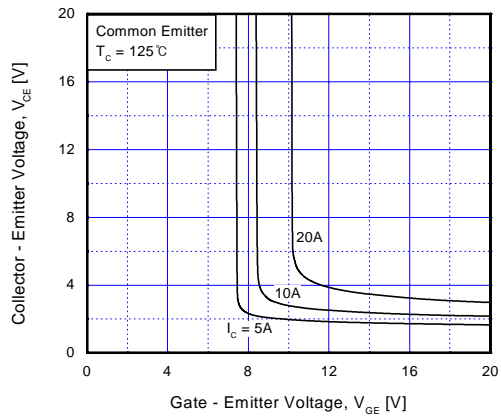
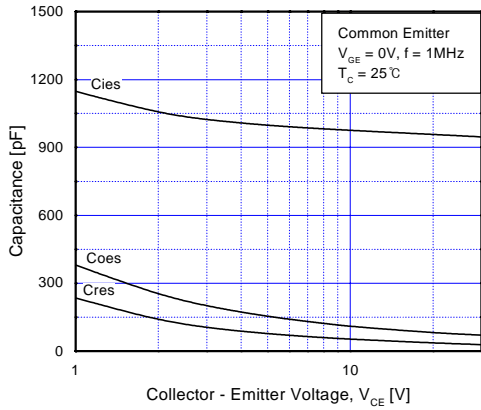
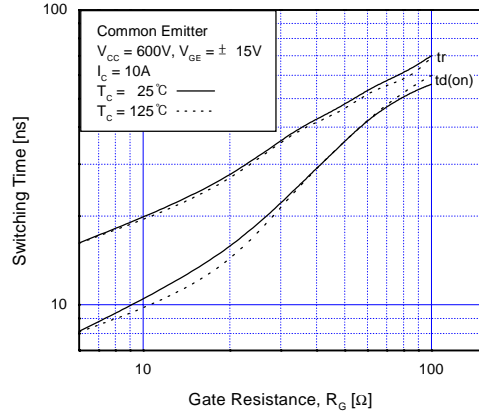


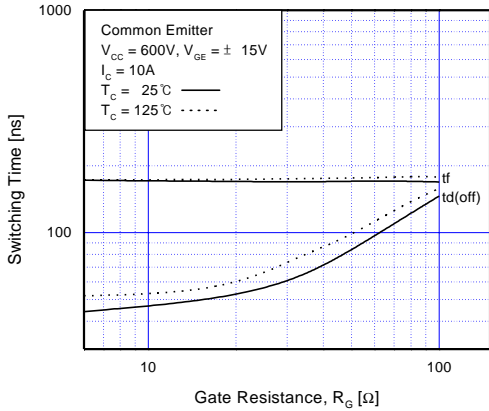
Fig 6. Saturation Voltage vs.  $V_{GE}$



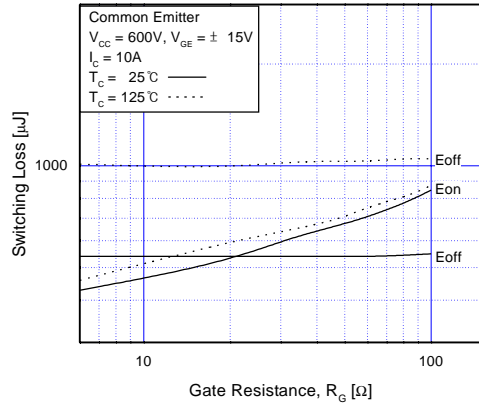
**Fig 7. Capacitance Characteristics**



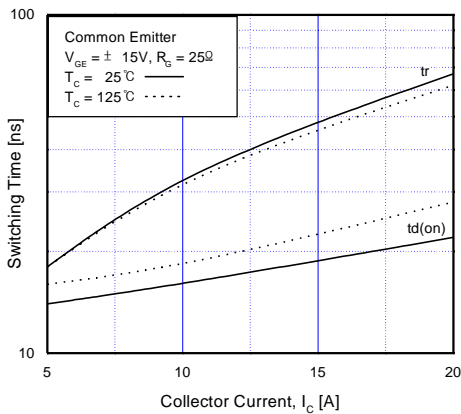
**Fig 8. Turn-On Characteristics vs. Gate Resistance**



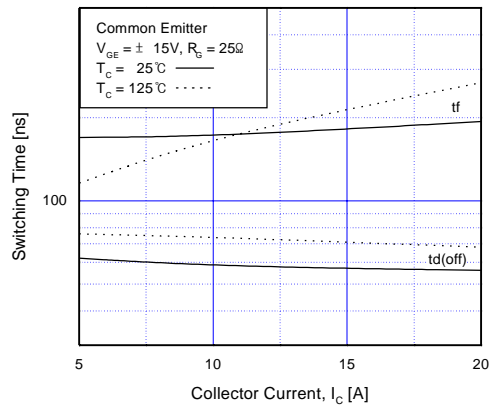
**Fig 9. Turn-Off Characteristics vs. Gate Resistance**



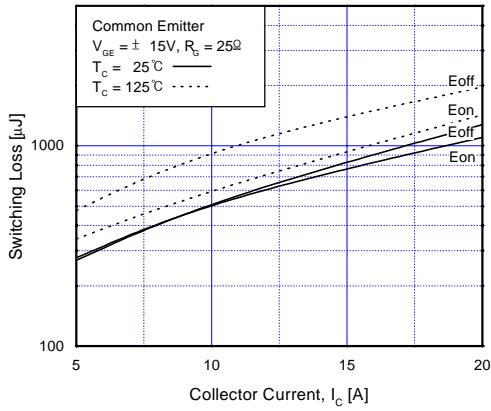
**Fig 10. Switching Loss vs. Gate Resistance**



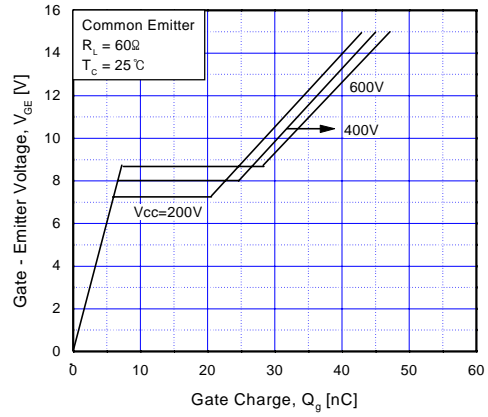
**Fig 11. Turn-On Characteristics vs. Collector Current**



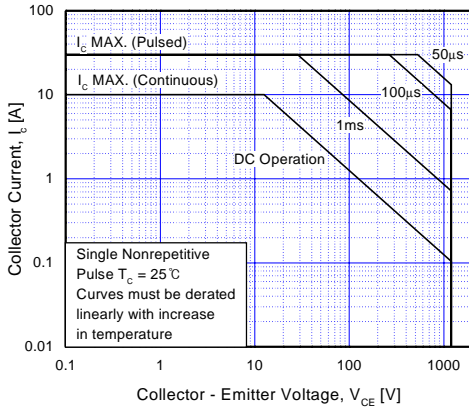
**Fig 12. Turn-Off Characteristics vs. Collector Current**



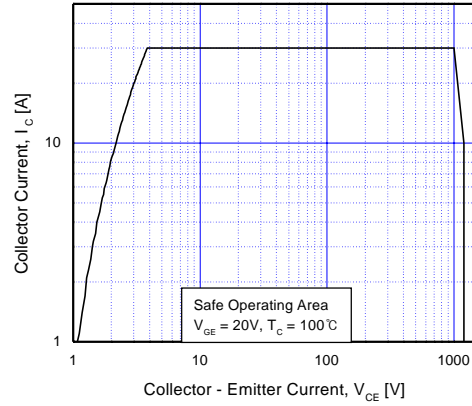
**Fig 13. Switching Loss vs. Collector Current**



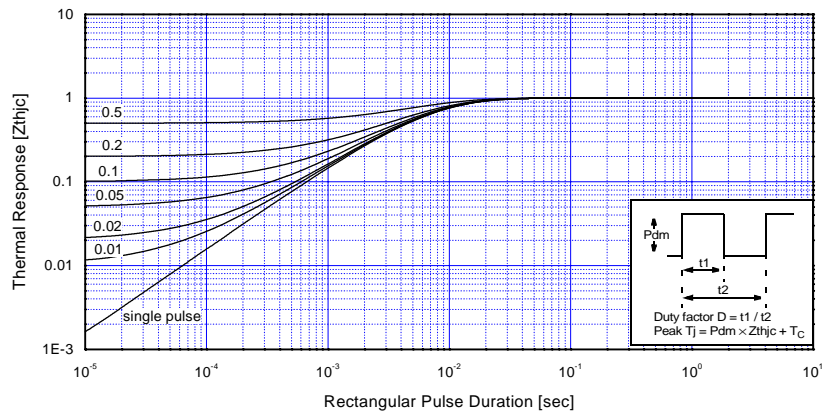
**Fig 14. Gate Charge Characteristics**



**Fig 15. SOA Characteristics**



**Fig 16. Turn-Off SOA**



**Fig 17. Transient Thermal Impedance of IGBT**

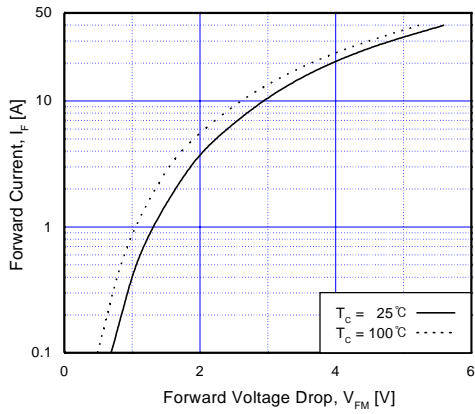


Fig 18. Forward Characteristics

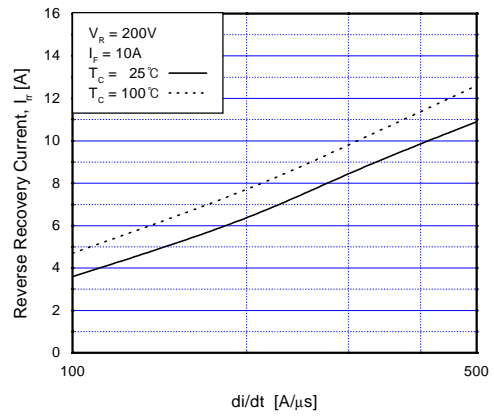


Fig 19. Reverse Recovery Current

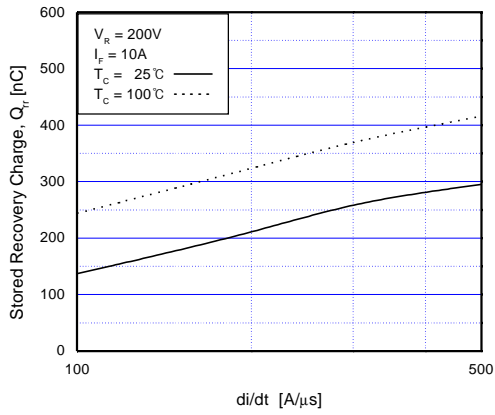


Fig 20. Stored Charge

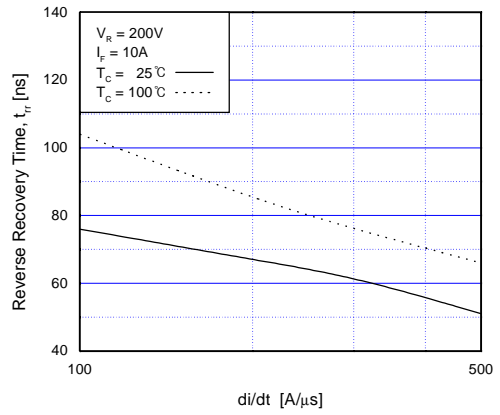
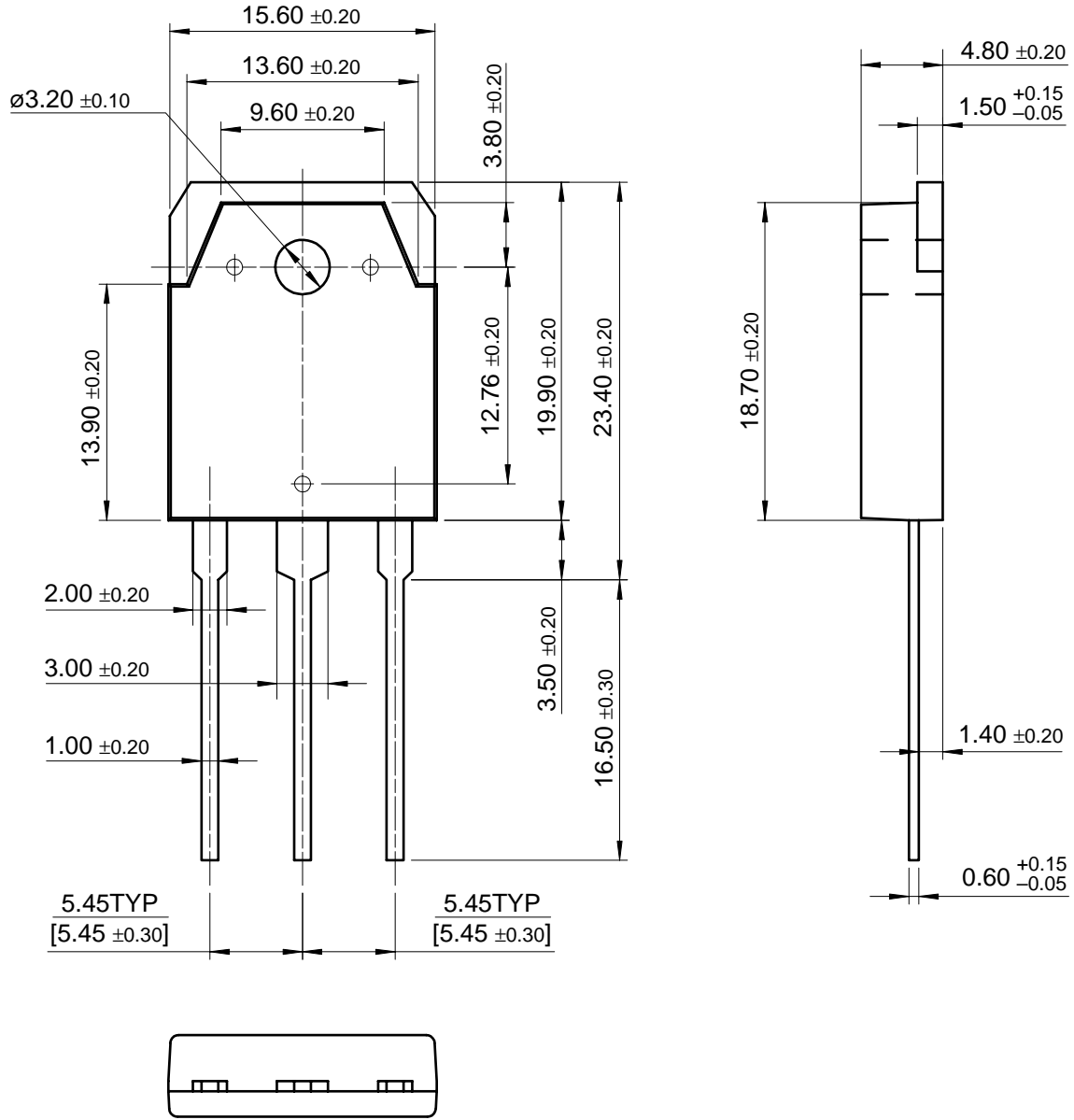


Fig 21. Reverse Recovery Time

Package Dimension

TO-3P (FS PKG CODE AF)



Dimensions in Millimeters

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DOMETM	HiSeC™	Power247™	SuperSOT™-3	
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